



N-Channel 30-V (D-S) Fast Switching MOSFET

PRODUCT SUMMARY

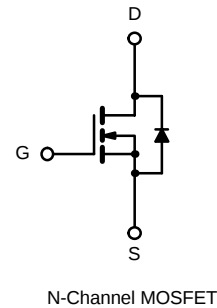
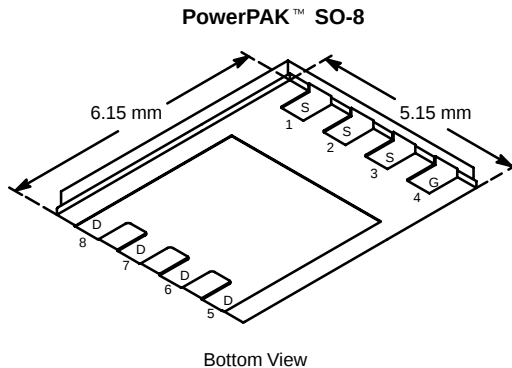
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0095 @ $V_{GS} = 10$ V	18
	0.014 @ $V_{GS} = 4.5$ V	15

FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK™ Package with Low 1.07-mm Profile

APPLICATIONS

- DC/DC Converters
- Optimized for “High-Side” Synchronous Rectifier Operation



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	18	11	A
	T _A = 70°C		14	8	
Pulsed Drain Current		I _{DM}	40		
Continuous Source Current (Diode Conduction) ^a		I _S	4.1	1.6	
Avalanche Current	L = 0.1 mH	I _{AS}	40		
Avalanche Energy		E _{AS}	80		mJ
Maximum Power Dissipation ^a	T _A = 25°C	P _D	5.0	1.9	W
	T _A = 70°C		3.2	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	20	25	$^\circ\text{C/W}$
	Steady State		52	65	
Maximum Junction-to-Case (Drain)		R_{thJC}	2.1	2.6	

Notes

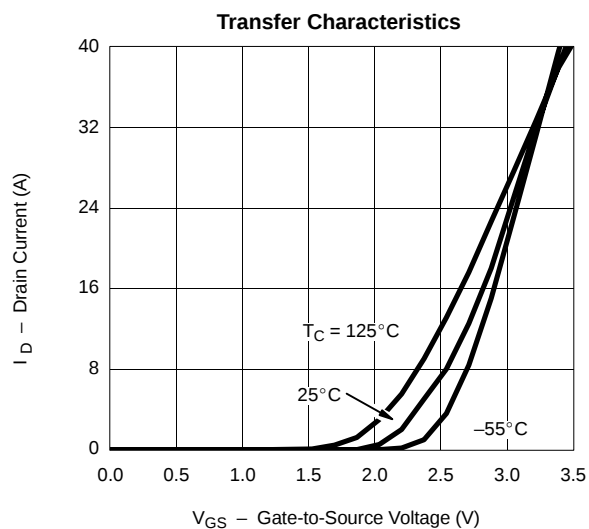
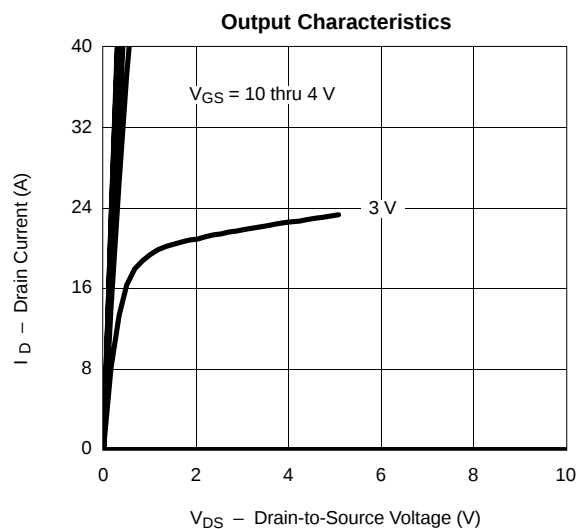
a. Surface Mounted on 1" x 1" FR4 Board.

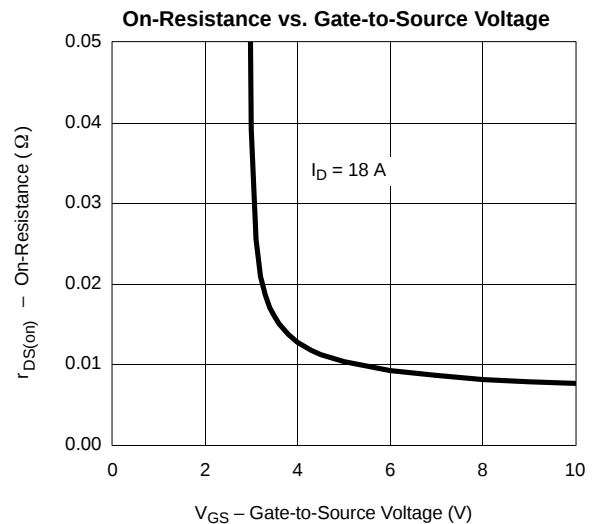
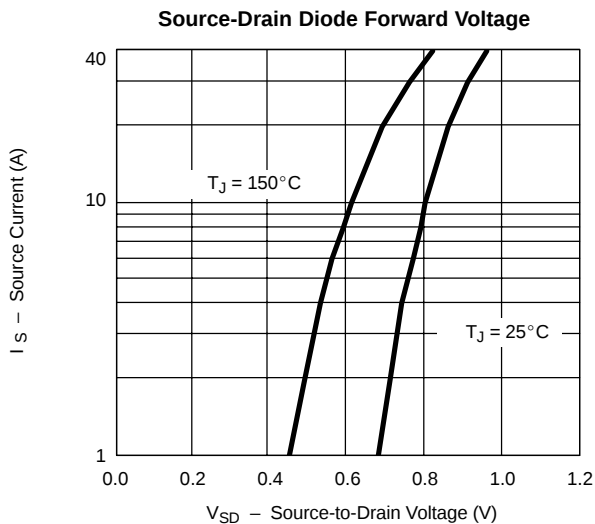
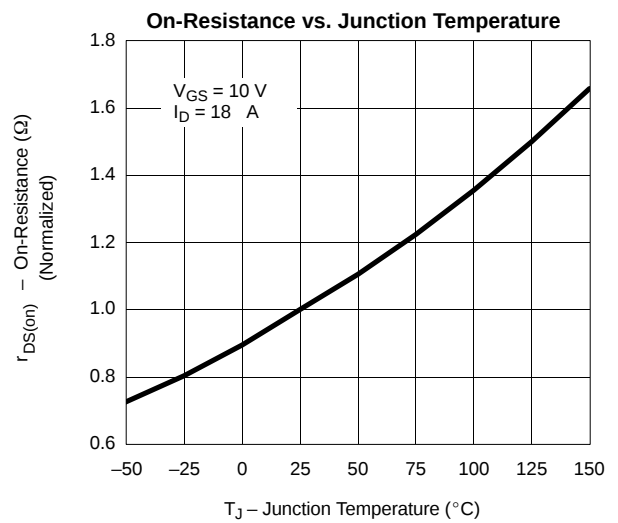
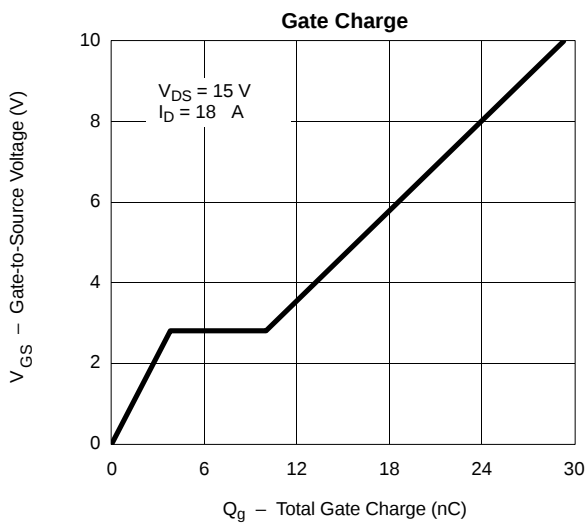
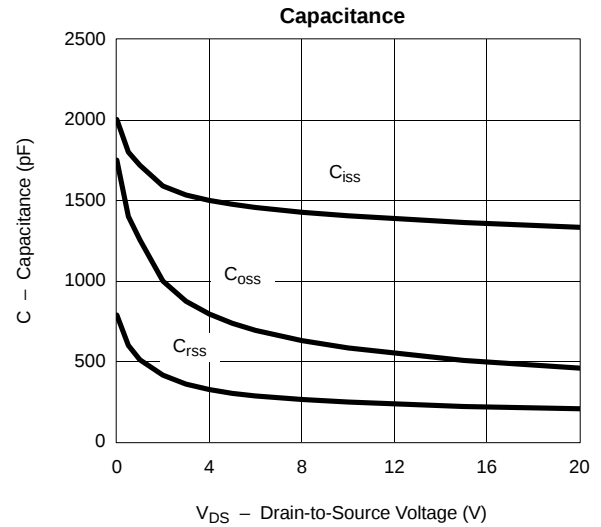
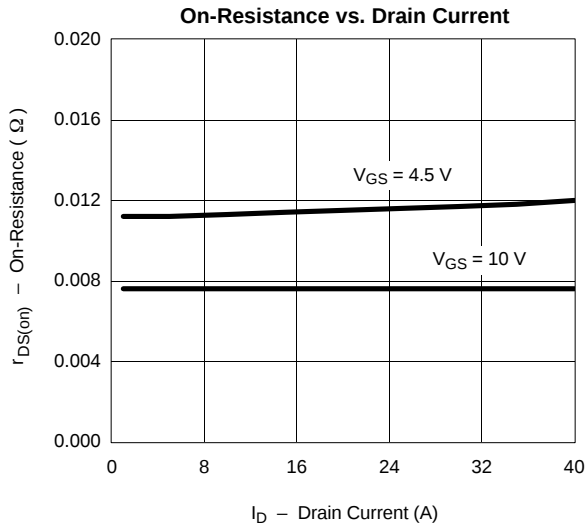
MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 24\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 18\ \text{A}$		0.0077	0.0095	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 15\ \text{A}$		0.0115	0.014	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 18\ \text{A}$		40		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 4.1\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 5.0\ \text{V}$, $I_D = 18\ \text{A}$		15.5	23	nC
Gate-Source Charge	Q_{gs}			3.8		
Gate-Drain Charge	Q_{gd}			6		
Gate-Resistance	R_G			0.8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		17	26	ns
Rise Time	t_r			14	21	
Turn-Off Delay Time	$t_{d(off)}$			39	60	
Fall Time	t_f			19	30	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 4.1\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		50	80	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)